



GP2M012A060H Information



For Reference Only

Part Number GP2M012A060H

ManufacturerGlobal Power Technologies GroupCategoryDiscrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 12A TO220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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GP2M012A060H Specifications

Manufacturer Part Number GP2M012A060H Manufacturer Global Power Technologies Group Category Discrete Semiconductor Products Fackage TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 12A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1890pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 231W (Tc) Rds On (Max) @ Id, Vgs 650 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 12A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1890pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 231W (Tc) Rds On (Max) @ Id, Vgs 650 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220	Manufacturer Part Number	GP2M012A060H
PackageTo-220-3Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1890pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)231W (Tc)Rds On (Max) @ Id, Vgs650 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220	Manufacturer	Global Power Technologies Group
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Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 12A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1890pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 231W (Tc) Rds On (Max) @ Id, Vgs 650 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600 VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10 VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs40nC @ 10 VInput Capacitance (Ciss) (Max) @ Vds1890pF @ 25 VVgs (Max)±30 VFET Feature-Power Dissipation (Max)231 W (Tc)Rds On (Max) @ Id, Vgs650 mOhm @ 6A, 10 VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1890pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)231W (Tc)Rds On (Max) @ Id, Vgs650 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220	Series	-
Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1890pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)231W (Tc)Rds On (Max) @ Id, Vgs650 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1890pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)231W (Tc)Rds On (Max) @ Id, Vgs650 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) $Vgs(th)$ (Max) @ Id SV @ $250\mu A$ Gate Charge (Qg) (Max) @ Vgs $Vgs(th)$ (Max) @ Vds $Vgs(th)$ (Max) @ Vds $Vgs(th)$ (Max) @ Vds $Vgs(th)$ (Max) @ Vds $Vgs(th)$ (Max) & $vgs(th)$ (Max) & $vgs(th)$ (Max) $Vgs(th)$ (Max) $Vgs(th)$ (Max) $Vgs(th)$ (Max) & $vgs(th)$ (Max) $Vgs($	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1890pF @ 25V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package 5V @ 250μA 40nC @ 10V 1890pF @ 25V 231W (Tc) 650 mOhm @ 6A, 10V 7-55°C ~ 150°C (TJ) Through Hole TO-220	Current - Continuous Drain (Id) @ 25°C	12A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature For Through Hole Supplier Device Package 40nC @ 10V 1890pF @ 25V 231W 1890pF @ 25V 231W 231W 170-220	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Coperating Type Through Hole Supplier Device Package 1890pF @ 25V 1890pF @ 25V 231W 50V 50V 50V 50V 50V 50V 50V 50	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)231W (Tc)Rds On (Max) @ Id, Vgs650 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220	Gate Charge (Qg) (Max) @ Vgs	40nC @ 10V
FET Feature - Power Dissipation (Max) 231W (Tc) Rds On (Max) @ Id, Vgs 650 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220	Input Capacitance (Ciss) (Max) @ Vds	1890pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 650 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs650 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220	Power Dissipation (Max)	231W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220	Rds On (Max) @ Id, Vgs	650 mOhm @ 6A, 10V
Supplier Device Package TO-220	Operating Temperature	-55°C ~ 150°C (TJ)
11	Mounting Type	Through Hole
Package / Case TO-220-3	Supplier Device Package	TO-220
	Package / Case	TO-220-3
Report errors?		Report errors?

GP2M012A060H Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

GP2M012A060H Payment Methods



















GP2M012A060H Shipping Methods













If you have any question about GP2M012A060H, please do not hesitate to contact us!

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